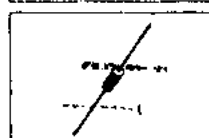




No.1898



**DSL10**

Diffused Junction Silicon Diode  
1.0A GENERAL-PURPOSE RECTIFIER APPLICATIONS

### Features

- . Plastic molded
- . Peak reverse voltage:  $V_{RM} = -100$  to  $-400V$
- . Average rectified current:  $I_o = 1.0A$

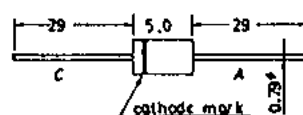
### Absolute Maximum Ratings at $T_a = 25^\circ C$

		DSL10B	DSL10C	DSL10E	unit
Peak Reverse Voltage	$V_{RM}$	-100	-200	-400	V
Average Rectified Current	$I_o$	→	→	1.0	A
Surge Forward Current	$I_{FSM}$ 50Hz sine wave 1 cycle	→	→	30	A
Junction Temperature	$T_j$	→	→	150	$^\circ C$
Storage Temperature	$T_{stg}$	→	-40 to +150		$^\circ C$

### Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Forward Voltage	$V_F$	$I_F = 1.0A$			1.2	V
Reverse Current	$I_R$	$V_R$ : Each $V_{RM}$			-10	$\mu A$

### Case Outline 1005 (unit:mm)

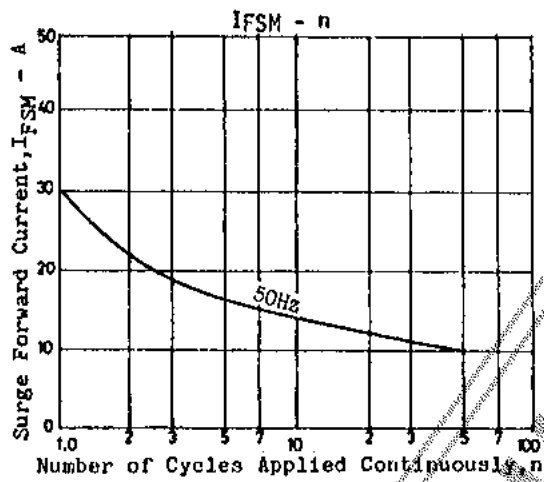
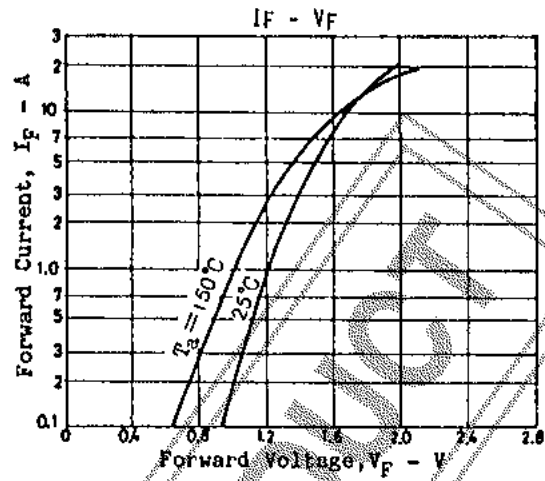
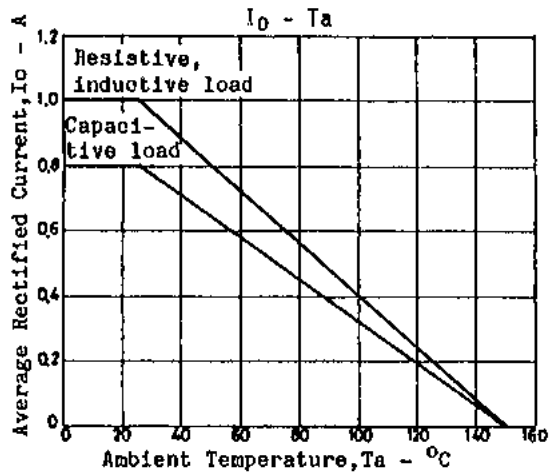


C: Cathode  
A: Anode

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DISCONTINUED PRODUCT